

/ Descriptions

WR0459I SQS Silicon PNP transistor in a TO-126F Plastic Package.

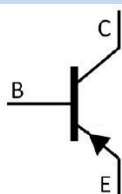
/ Features

5VF4495I
Complementary pair with 2SC1162F.

/ Applications

Low frequency power amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

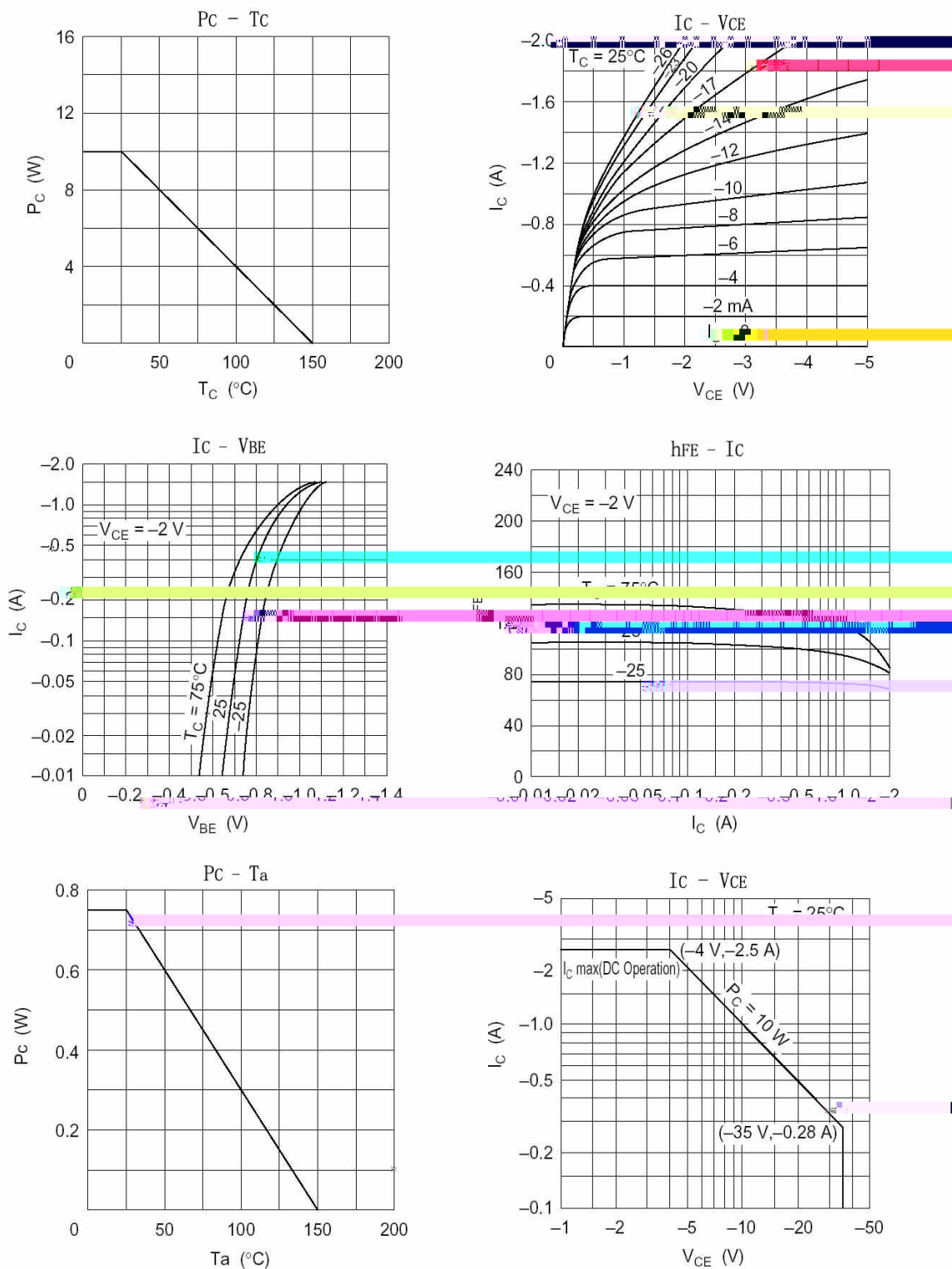
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	B	C	D
h_{FE} Range	60 120	100 200	160 320

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-35	V
Collector to Emitter Voltage	V_{CEO}	-35	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-2.5	A
Collector Current – Continuous(Pulse)	I_{CP}	-3	A
Collector Power Dissipation	P_C	750	mW
Collector Power Dissipation	$P_C(T_c=25^\circ\text{C})$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown	V_{CBO}	$I_C = -1\text{mA}$ $I_E = 0$	-35			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -10\text{mA}$ $R_{BE} = \infty$	-35			V

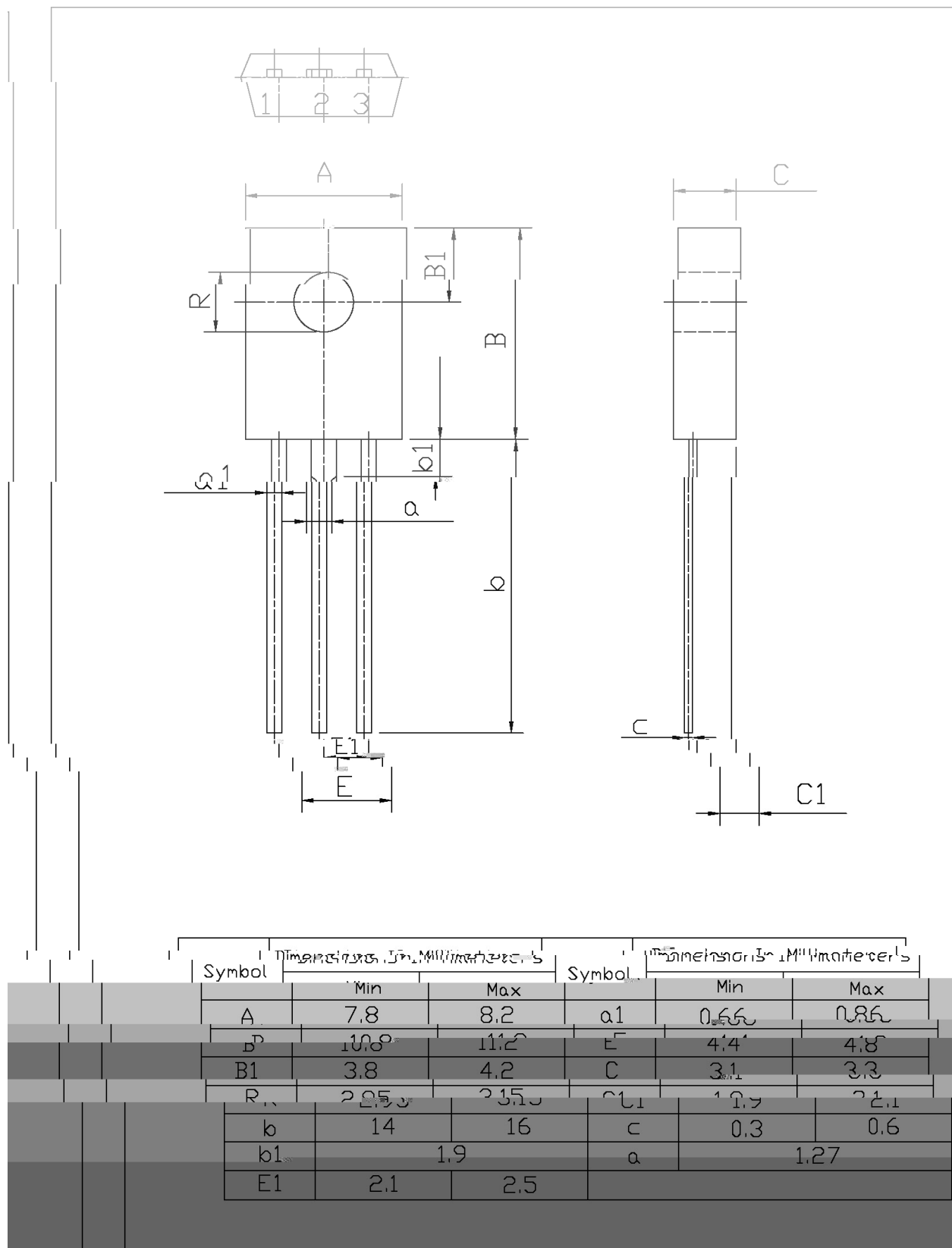
/ **Electrical Characteristic Curve**



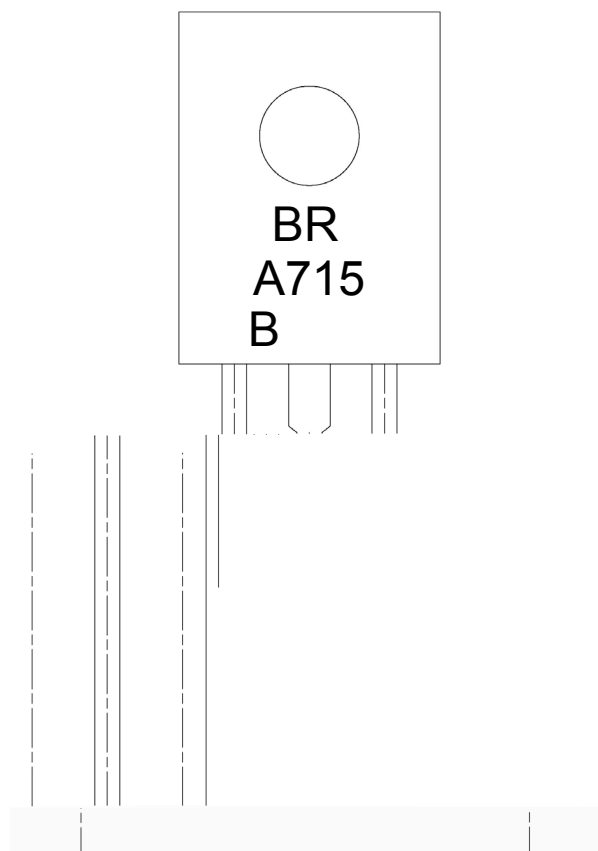
/ Package Dimensions

1U-126T

单位: mm



/ Marking Instructions



EU

D: 48

E: k_{IH}

Note:

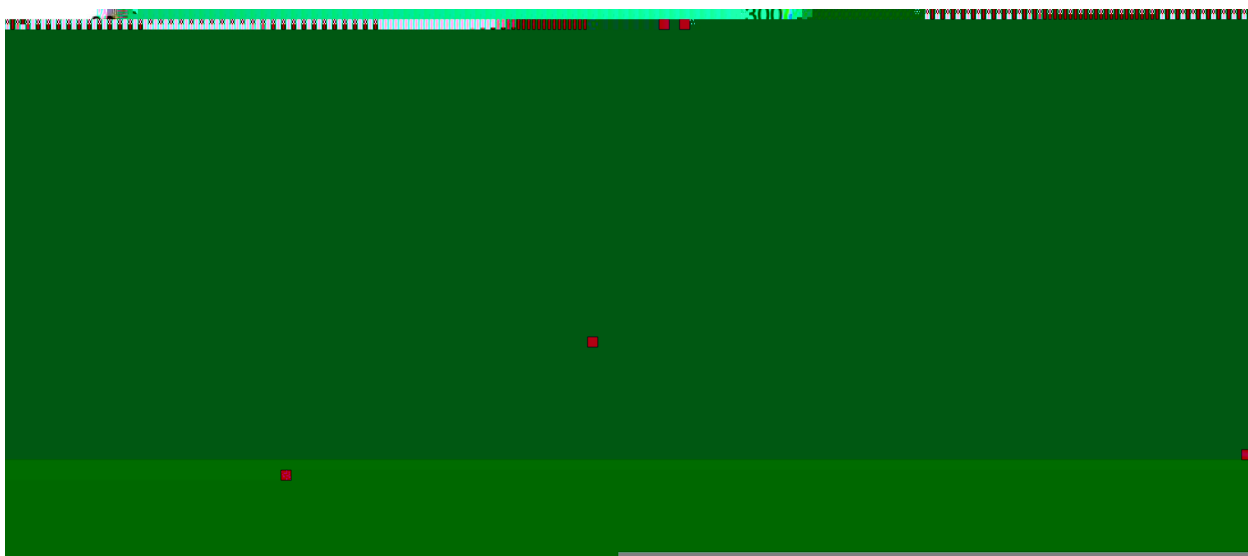
BR: Company Code

A715: Product Type.

B: h_{FE} Classifications Symbol

***: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-----|------|----|-----------|---|
| 1 | 25 | 150% | 60 | 90sec; | 1.Preheating:25~150%, Time:60~90sec. |
| 2 | 255 | ± 5% | 5 | ± 0.5sec; | 2.Peak Temp.:255 ± 5%, Duration:5 ± 0.5sec. |
| 3 | | | 2 | 10%/sec. | 3. Cooling Speed: 2~10%/sec. |

/ Resistance to Soldering Heat Test Conditions

270 ± 5% 10 ± 1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		